electrode[, which are disposed on a surface and the other surface of said semiconductor thin film sandwiching an insulating film,] <u>on an opposite side of said semiconductor thin film,</u>

[wherein said first gate electrode and said second gate electrode receive a first gate voltage and a second gate voltage, respectively, through wirings which are separately provided,

wherein said first gate electrode on-off controls said channel depending on said first gate voltage, and

wherein said second gate electrode actively controls said threshold voltage depending on said second gate voltage to adjust the on-off operation of said thin film transistors.]

<u>and further comprising a means for adjusting the threshold voltage by applying a first threshold adjustment voltage to the second gate electrode when the first gate electrode receives a first control voltage and applying a second threshold adjustment voltage to the second gate electrode when the first electrode receives a second control voltage.</u>

2. (Once Amended) The semiconductor apparatus according to claim 1, wherein said semiconductor thin film constituting said channel is comprised of polycrystalline silicon which does not contain an impurity [effectively affecting the formation of a depletion layer], and has a thickness of 100 nm or less.

4. Please cancel claim 4.

5. Please cancel claim 5.

CLEAN VERSION OF CLAIMS

1. A display apparatus comprising:

a plurality of thin film transistors, each of said thin film transistor comprising a semiconductor thin film constituting a channel and having a threshold voltage, and a first gate electrode on one side of said semiconductor thin film and a second gate electrode on an opposite side of said semiconductor thin film,

and further comprising a means for adjusting the threshold voltage by applying a first threshold adjustment voltage to the second gate electrode when the first gate electrode receives a first control voltage and applying a second threshold adjustment voltage to the second gate electrode when the first electrode receives a second control voltage.

2. The semiconductor apparatus according to claim 1, wherein said semiconductor thin film constituting said channel is comprised of polycrystalline silicon which does not contain an impurity, and has a thickness of 100 nm or less.